

ATTACHMENT - CLAIM CHANGES

3. (Twice Amended) A semiconductor integrated circuit device, comprising:
- a source region formed on a semiconductor substrate;
 - a first conductor having a first resistivity formed over said source region;
 - a first contact group having contacts connecting said source region and said first conductor;
 - a second conductor having a second resistivity over said first conductor;
 - a second contact group having contacts connecting said first conductor and said second conductor;
 - a drain region formed on said semiconductor substrate;
 - a third conductor having said first resistivity formed over said drain region;
 - a third contact group having contacts connecting said drain region and said third conductor;
 - a fourth conductor having said second resistivity formed over said third conductor;
 - a fourth contact group having contacts connecting said third conductor and said fourth conductor;
- wherein a total number of contacts in said first contact group is different from a total number of contacts in said second contact group, and
- a total number of contacts in said third contact [hole] group is different from a total number of contacts in said fourth contact group.

5. (Twice Amended) The semiconductor integrated circuit device as claimed in claim 4, wherein said [fist] first resistivity is higher than said second resistivity, and a total number of contacts in said first contact group and in said third contact group is greater than a total number of contacts in said second contact group and in said fourth contact group.

20. (Amended) A transistor according to claim 16, wherein a distance from an end of the source region to a nearest one of the first contacts is equal to [one] or greater than a distance from the gate electrode to said nearest one of the first contacts.